

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

TAKITA et al.

Serial No. 09/046,671

Art Unit: 2823

Filed: March 24, 1998

Examiner: Eaton, K.

For: SEMICONDUCTOR DEVICE AND METHOD FOR FABRICATING THE SAME

RESPONSE UNDER 37 CFR § 1.116

Commissioner for Patents
Washington, D.C. 20231

February 21, 2001

Sir:

In response to the Office Action mailed September 12, 2000, having been duly extended from December 12, 2000, until March 12, 2001, by the attached Petition for Extension of Time, please amend the above-identified application as set forth below.

IN THE CLAIMS

Please amend the claims as follows.

1. (Amended) A semiconductor device comprising:
a lightly doped semiconductor substrate of a first conduction type;
a buried semiconductor layer of a second conduction type formed in a first region of the semiconductor substrate, spaced from a surface of the semiconductor substrate;
a semiconductor region of the second conduction type extending from the surface of the semiconductor substrate to a peripheral portion of the buried semiconductor layer and;
a semiconductor region of the first conduction type formed in the semiconductor substrate surrounded by the buried semiconductor layer and the semiconductor region of